

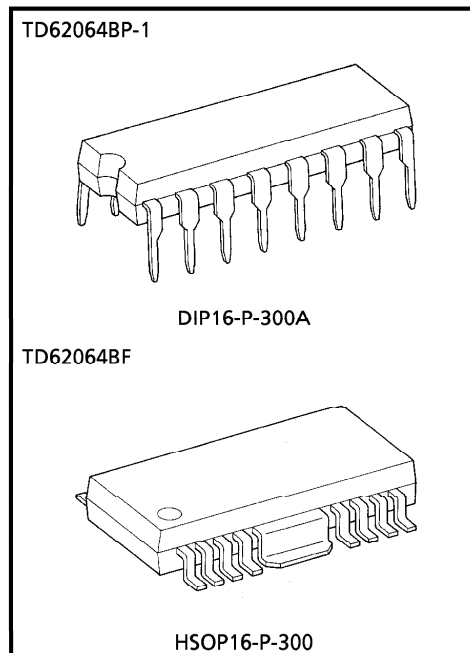
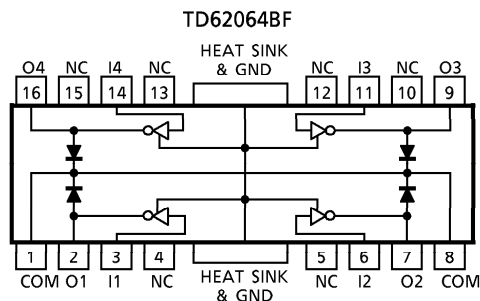
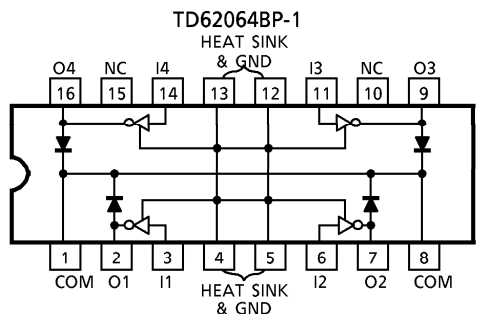
## 4ch HIGH-CURRENT DARLINGTON SINK DRIVER

The TD62064BP-1 and TD62064BF are high-voltage, high-current darlington drivers comprised of four NPN darlington pairs.  
All units feature integral clamp diodes for switching inductive loads.  
Applications include relay, hammer, lamp and stepping motor drivers.

### FEATURES

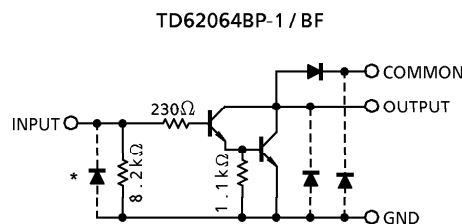
- Package Type BP-1 : DIP16 pin  
BF : PFP16 pin
- High Output Sustaining Voltage :  $V_{CE(SUS)} = 80V$  (Min.)
- Output Current (Single Output) :  $I_{OUT} = 1.5A / ch$  (Max.)
- Output Clamp Diodes
- Input Compatible with TTL and 5V CMOS
- GND and SUB Terminal = Heat Sink

### PIN CONNECTION (TOP VIEW)



Weight DIP16-P-300A : 1.11g (Typ.)  
HSOP16-P-300 : 0.50g (Typ.)

### SCHEMATICS (EACH DRIVER)



\* : Parasitic

The input and output parasitic diodes cannot be used as clamp diodes.

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**MAXIMUM RATINGS (Ta = 25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Output Sustaining Voltage	V <sub>CE(SUS)</sub>	-0.5 ~ 80	V
Parasitic Transistor Output Voltage	V <sub>CEF</sub> *1	80	V
Output Current	I <sub>OUT</sub>	1.5	A / ch
Input Current	I <sub>IN</sub>	50	mA
Input Voltage	V <sub>IN</sub>	7	V
Clamp Diode Reverse Voltage	V <sub>R</sub>	80	V
Clamp Diode Forward Current	I <sub>F</sub>	1.5	A
Power Dissipation	BP-1	1.47 / 2.7 *2	W
	BF	0.9 / 1.4 *3	
Operating Temperature	T <sub>opr</sub>	-40 ~ 85	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ 150	°C

- \*1 Parasitic Transistor (COMMON - GND - OUTPUT) Output Voltage
- \*2 On Glass Epoxy PCB (50×50×1.6mm Cu 50%)
- \*3 On Glass Epoxy PCB (60×30×1.6mm Cu 30%)

**RECOMMENDED OPERATING CONDITIONS (Ta = -40~85°C)**

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT	
Output Sustaining Voltage	V <sub>CE(SUS)</sub>		0	—	80	V	
Output Current	I <sub>OUT</sub>	DC 1 Circuit, Ta = 25°C	0	—	1250	mA / ch	
		T <sub>pw</sub> = 25ms 4 Circuits	Duty = 10%	0	—		1250
			Duty = 50%	0	—		380
		T <sub>j</sub> = 120°C Ta = 85°C	Duty = 10%	0	—		900
Duty = 50%	0		—	170			
Input Voltage	V <sub>IN</sub>		0	—	8	V	
	(Output On) V <sub>IN(ON)</sub>	I <sub>OUT</sub> = 1.25A	2.5	—	8	V	
	(Output Off) V <sub>IN(OFF)</sub>		0	—	0.4	V	
Input Current	I <sub>IN</sub>		0	—	20	mA	
Clamp Diode Reverse Voltage	V <sub>R</sub>		0	—	80	V	
Clamp Diode Forward Current	I <sub>F</sub>		—	—	1.25	A	
Power Dissipation	BP-1	Ta = 85°C *1	—	—	1.4	W	
	BF	Ta = 85°C *2	—	—	0.7		

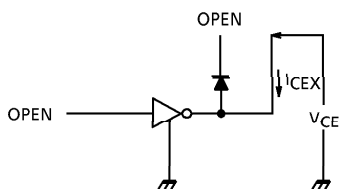
- \*1 On Glass Epoxy PCB (50×50×1.6mm Cu 50%)
- \*2 On Glass Epoxy PCB (60×30×1.6mm Cu 30%)

**ELECTRICAL CHARACTERISTICS** ( $T_a = 25^\circ\text{C}$  unless otherwise noted)

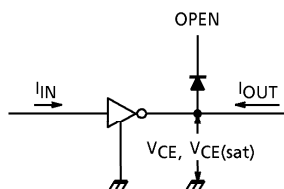
CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Leakage Current	$I_{CEX}$	1	$V_{CE} = 80\text{V}$ , $T_a = 25^\circ\text{C}$	—	—	50	$\mu\text{A}$
			$V_{CE} = 80\text{V}$ , $T_a = 85^\circ\text{C}$	—	—	100	
Output Saturation Voltage	$V_{CE(sat)}$	2	$I_{OUT} = 1.25\text{A}$ , $V_{IN} = 2.4\text{V}$	—	—	1.6	V
			$I_{OUT} = 0.75\text{A}$ , $V_{IN} = 2.4\text{V}$	—	—	1.25	
DC Current Transfer Ratio	$h_{FE}$	2	$V_{CE} = 2\text{V}$ , $I_{OUT} = 1.25\text{A}$	—	1500	—	
Input Voltage (Output On)	$V_{IN(ON)}$	3	$I_{OUT} = 1.25\text{A}$ , $I_{IN} = 2\text{mA}$	—	—	2.4	V
Clamp Diode Leakage Current	$I_R$	4	$V_R = 80\text{V}$ , $T_a = 25^\circ\text{C}$	—	—	50	$\mu\text{A}$
			$V_R = 80\text{V}$ , $T_a = 85^\circ\text{C}$	—	—	100	
Clamp Diode Forward Voltage	$V_F$	5	$I_F = 1.25\text{A}$	—	1.5	2.0	V
Input Capacitance	$C_{IN}$	6	$V_{IN} = 0$ , $f = 1\text{MHz}$	—	15	—	pF
Turn-On Delay	$t_{ON}$	7	$V_{OUT} = 80\text{V}$ , $R_L = 68\Omega$	—	0.1	—	$\mu\text{s}$
Turn-Off Delay	$t_{OFF}$			—	1.0	—	
Parasitic Transistor Output Voltage	$V_{CEF}$	8	$I_{CEF} = 150\text{mA}$	80	—	—	V

**TEST CIRCUIT**

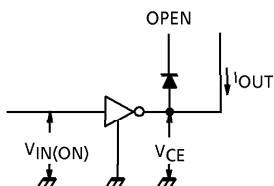
1.  $I_{CEX}$



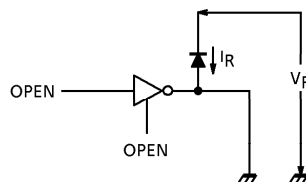
2.  $V_{CE(sat)}$ ,  $h_{FE}$



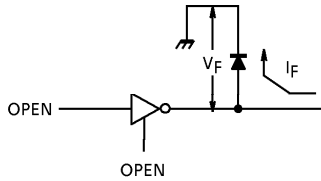
3.  $V_{IN(ON)}$



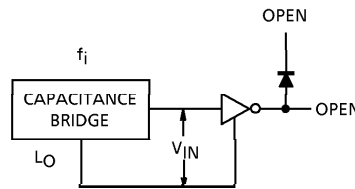
4.  $I_R$



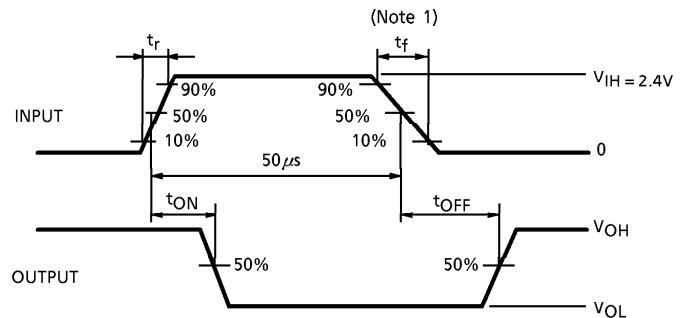
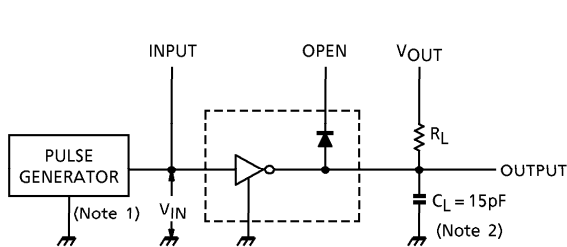
5.  $V_F$



6.  $C_{IN}$



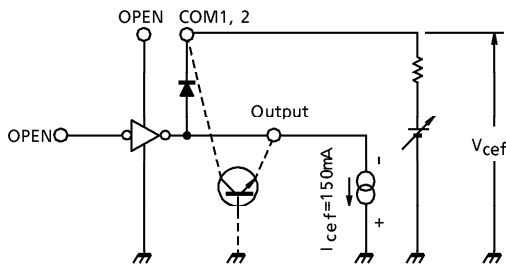
7.  $t_{ON}$ ,  $t_{OFF}$



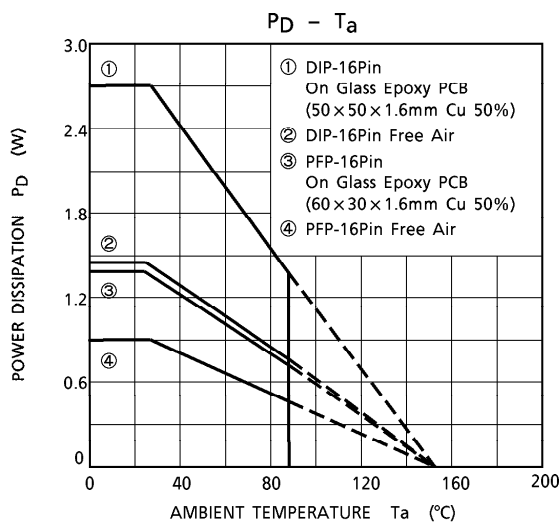
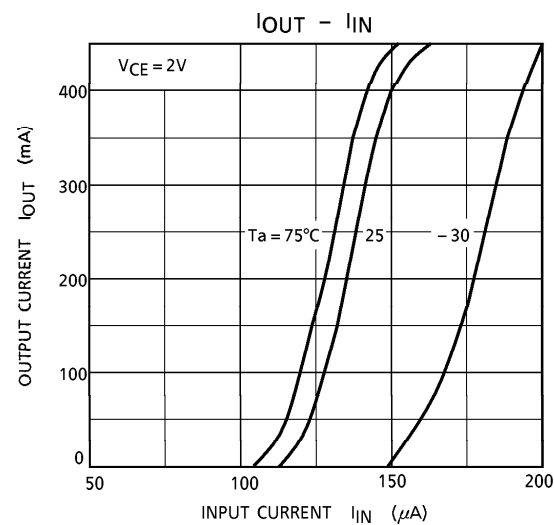
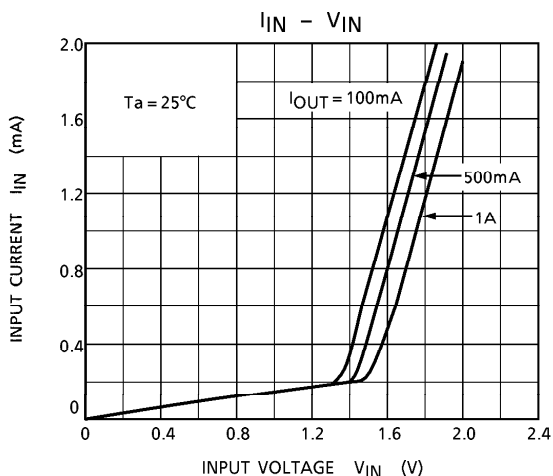
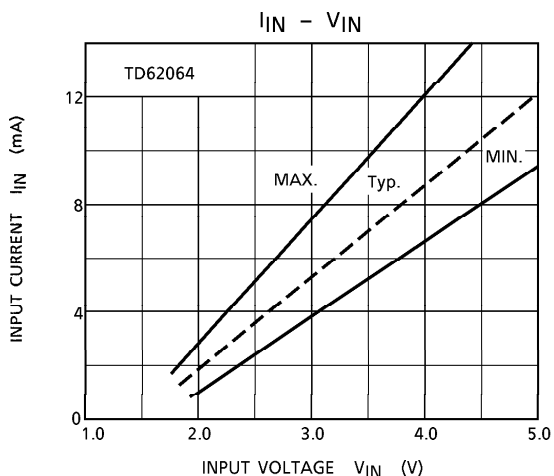
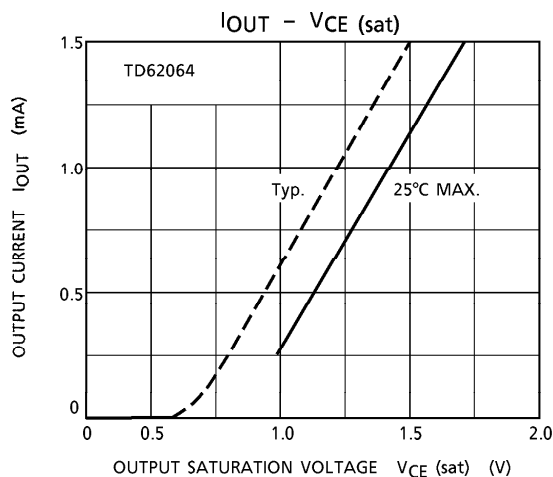
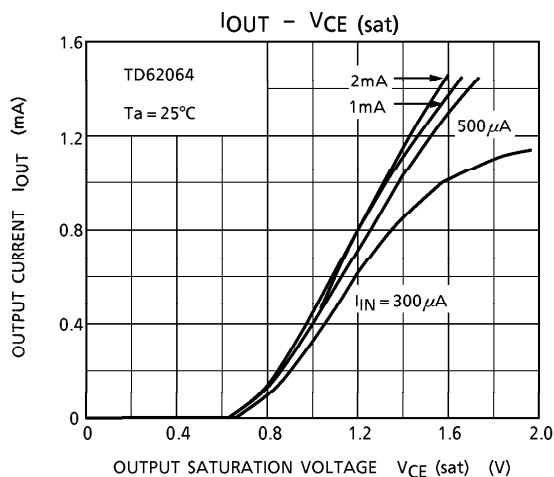
(Note 1) Pulse Width  $50\mu s$ , Duty Cycle 10%  
Output Impedance  $50\Omega$ ,  $t_r \leq 5ns$ ,  $t_f \leq 10ns$

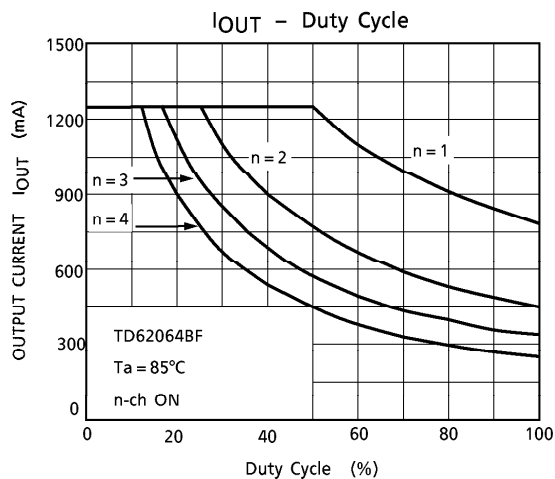
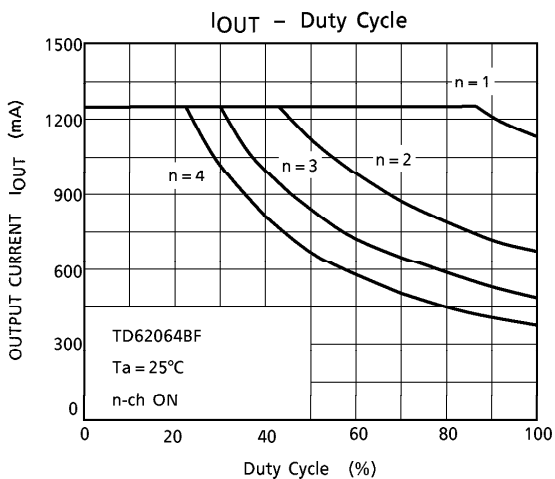
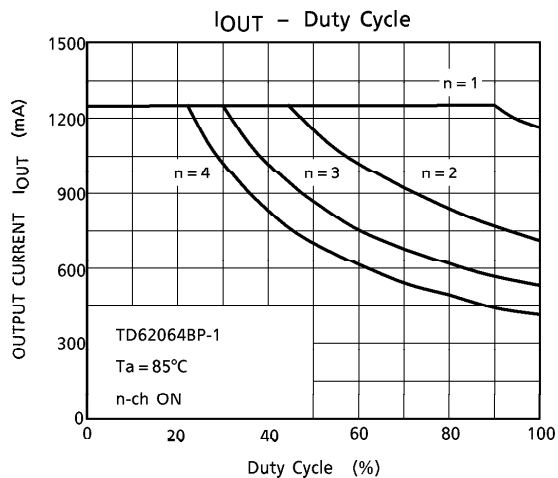
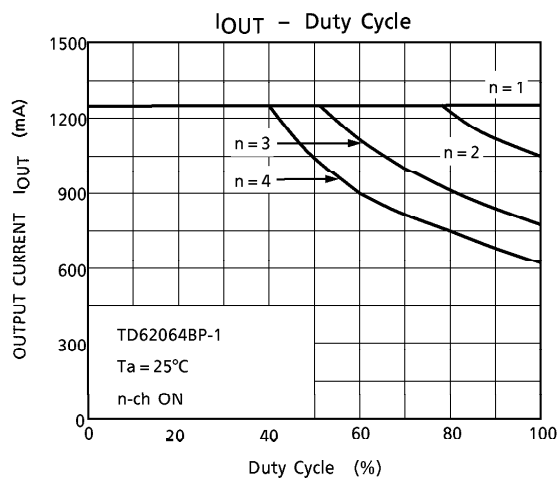
(Note 2)  $C_L$  includes probe and jig capacitance

8.  $V_{cef}$



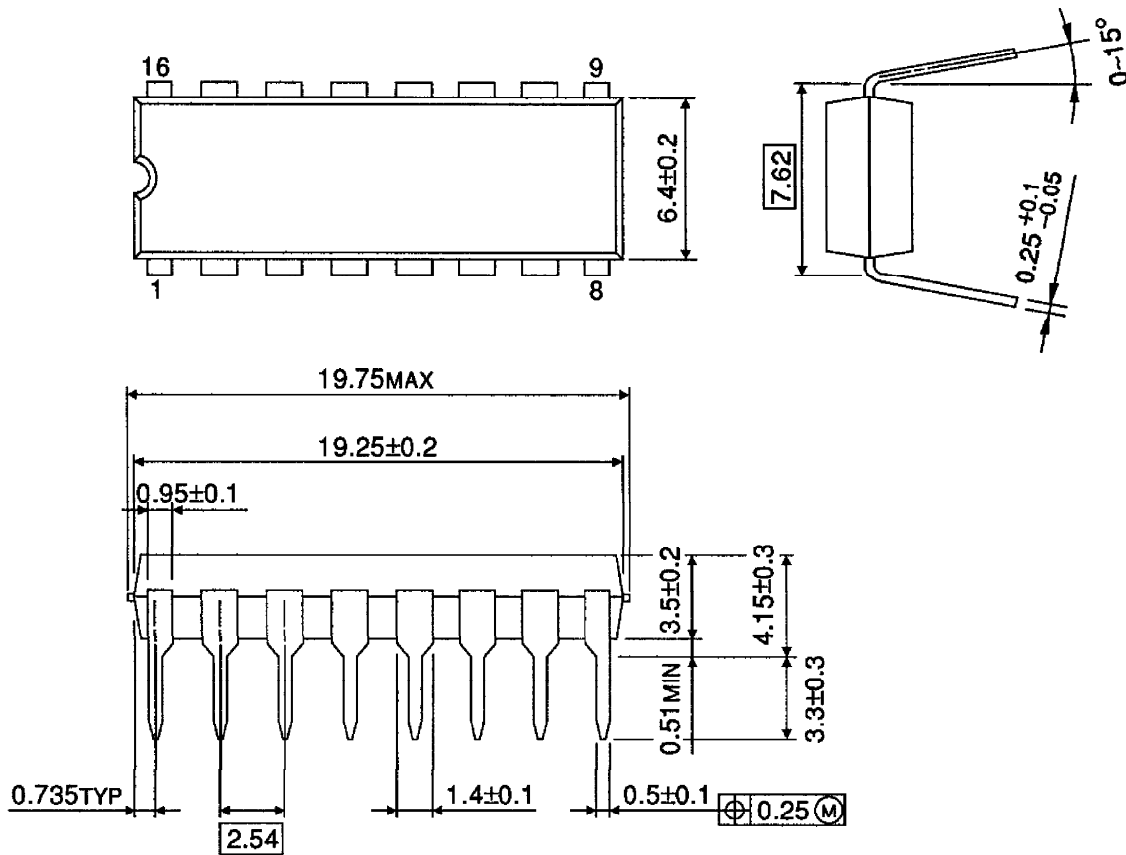
$I_{cef} = 150mA$  (at . Single pulse = 5ms)





**OUTLINE DRAWING**  
DIP16-P-300A

Unit : mm

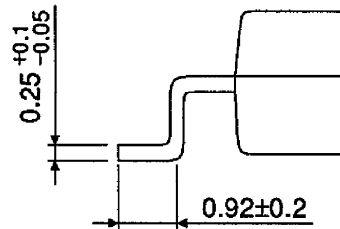
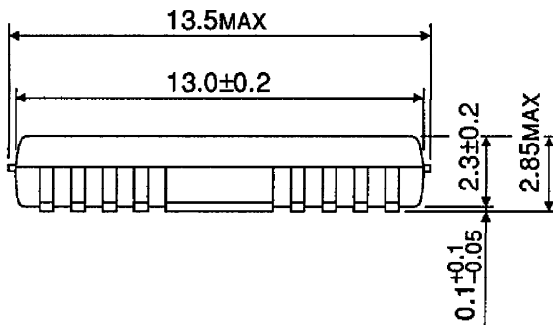
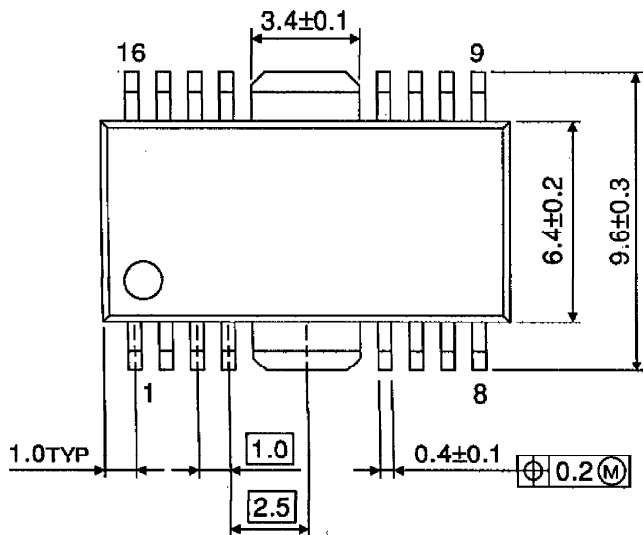


Weight : 1.11g (Typ.)

TD62064BP-1 - 7
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**OUTLINE DRAWING**  
HSOP16-P-300

Unit : mm



Weight : 0.50g (Typ.)

TD62064BP-1 - 8*
1994 - 3 - 8
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